RLD INTELLECTUAL PROPERTY ORGANIZAT



INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classificati n 7: C30B 25/14, 25/02

(11) International Publication Number: A1

WO 00/70129

(43) International Publication Date: 23 November 2000 (23.11.00)

(21) International Application Number:

PCT/GB00/01829

(22) International Filing Date:

12 May 2000 (12.05.00)

(30) Priority Data:

99303738.1

13 May 1999 (13.05.99)

EP

(71) Applicant (for all designated States except US): EMF IRE-LAND LIMITED [IE/IE]; The Crestfield Centre, Riverstown, Glanmire, County Cork (IE).

(72) Inventor; and

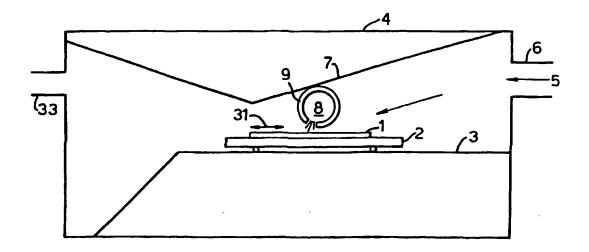
- (75) Inventor/Applicant (for US only): ROBINSON, Michael. Franks [GB/GB]; Wynfor, Church Road, Wentworth, Ely, Cambridgeshire CB6 3QE (GB).
- (74) Agent: GILL JENNINGS & EVERY; Broadgate House, 7 Eldon Street, London EC2M 7LH (GB).

(81) Designated States: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published

With international search report.

(54) Title: METHOD AND APPARATUS FOR EPITAXIALLY GROWING A MATERIAL ON A SUBSTRATE



(57) Abstract

A method of epitaxially growing a material on a substrate (1). The method comprises separately heating precursors to their respective decomposition temperatures at or adjacent a region of the substrate to generate species which are supplied separately to the region and which combine at the region.

. ₫ 8